

TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U-MOS IV)

TPCF8304

Notebook PC Applications

Portable Equipment Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 60 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 5.9 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = -10 \text{ }\mu\text{A}$ (max) ($V_{DS} = -30 \text{ V}$)
- Enhancement model: $V_{th} = -0.8$ to -2.0 V , ($V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

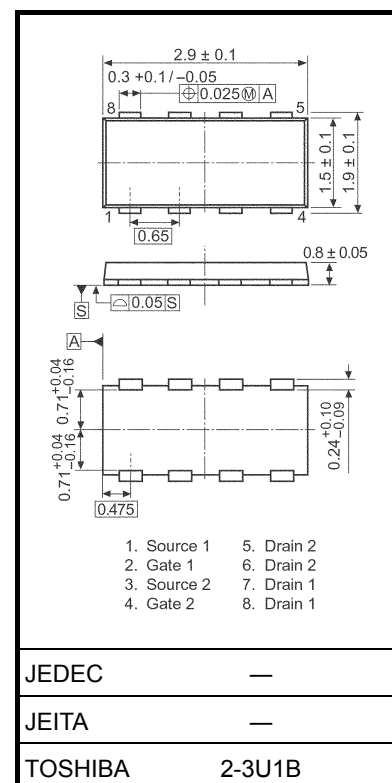
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	-30	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	-3.2	A
	Pulse (Note 1)	I_{DP}	-12.8	
Drain power dissipation ($t = 5 \text{ s}$) (Note 2a)	Single-device operation (Note 3a)	$P_D (1)$	1.35	W
	Single-device value at dual operation (Note 3b)	$P_D (2)$	1.12	
Drain power dissipation ($t = 5 \text{ s}$) (Note 2b)	Single-device operation (Note 3a)	$P_D (1)$	0.53	
	Single-device value at dual operation (Note 3b)	$P_D (2)$	0.33	
Single-pulse avalanche energy (Note 4)		E_{AS}	0.67	mJ
Avalanche current		I_{AR}	-1.6	A
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		E_{AR}	0.11	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~150	$^\circ\text{C}$

Note: For Notes 1 to 6, see the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Caution: This transistor is an electrostatic-sensitive device. Handle with care.

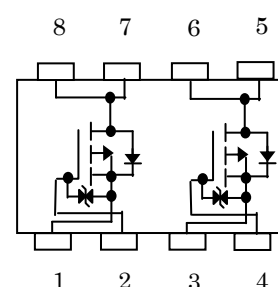
Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-3U1B

Weight: 0.011 g (typ.)

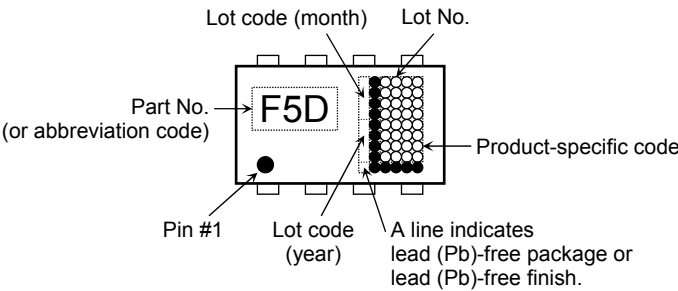
Circuit Configuration



Thermal Characteristics

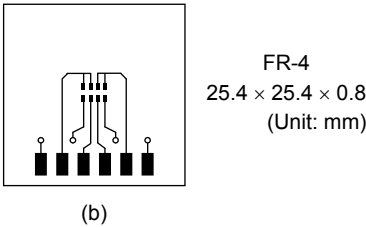
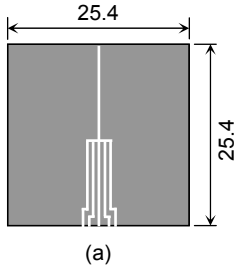
Characteristic		Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	Single-device operation (Note 3a)	$R_{th} (ch-a) (1)$	92.6	°C/W
	Single-device value at dual operation (Note 3b)	$R_{th} (ch-a) (2)$	111.6	
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	Single-device operation (Note 3a)	$R_{th} (ch-a) (1)$	235.8	°C/W
	Single-device value at dual operation (Note 3b)	$R_{th} (ch-a) (2)$	378.8	

Marking (Note 6)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



Note 3: a) The power dissipation and thermal resistance values shown are for a single device. (During single-device operation, power is applied to one device only.)

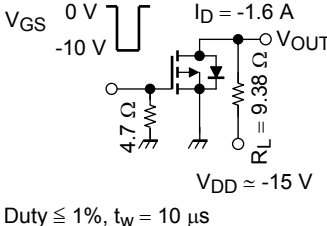
b) The power dissipation and thermal resistance values shown are for a single device. (During dual operation, power is evenly applied to both devices.)

Note 4: $V_{DD} = -24 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 0.2 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = -1.6 \text{ A}$

Note 5: Repetitive rating; pulse width limited by max channel temperature

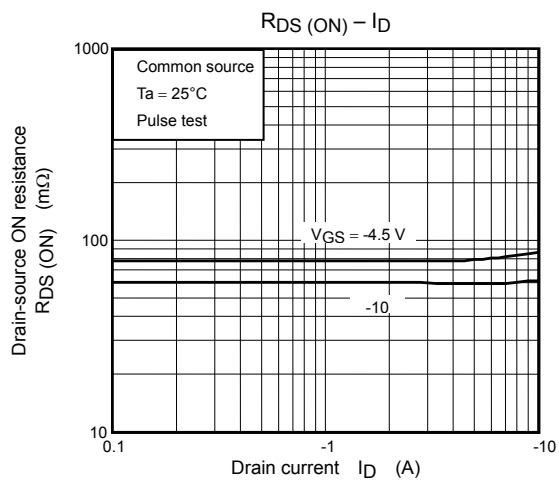
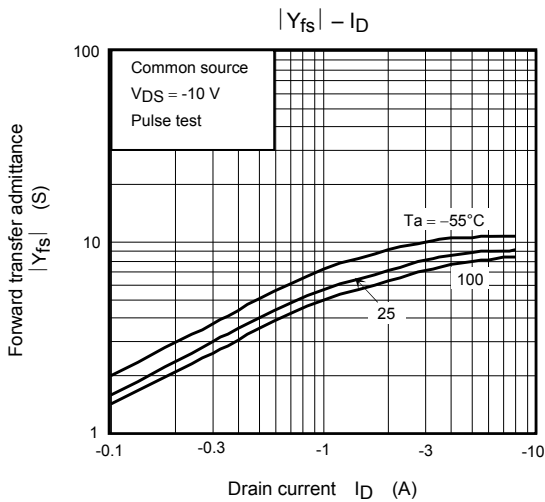
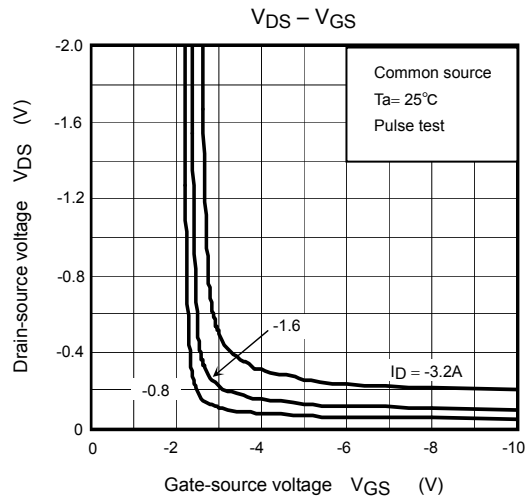
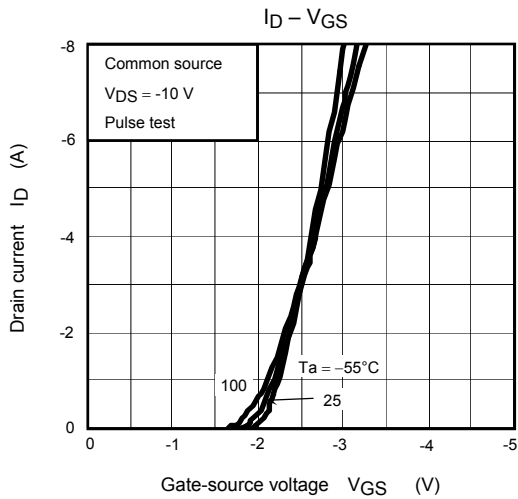
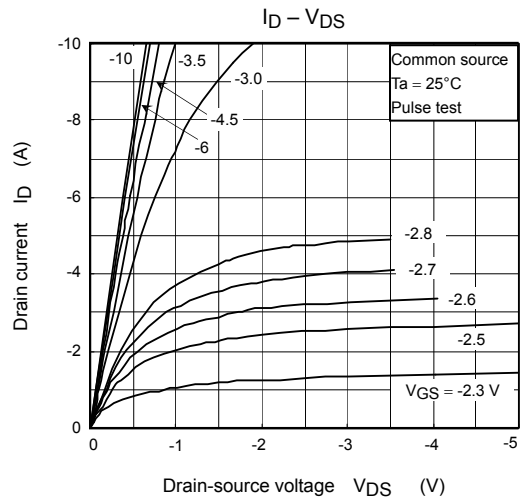
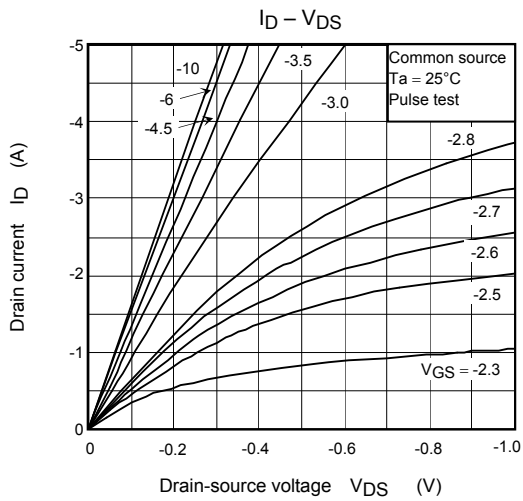
Note 6: ● to the lower left of the Part No. marking indicates Pin 1.

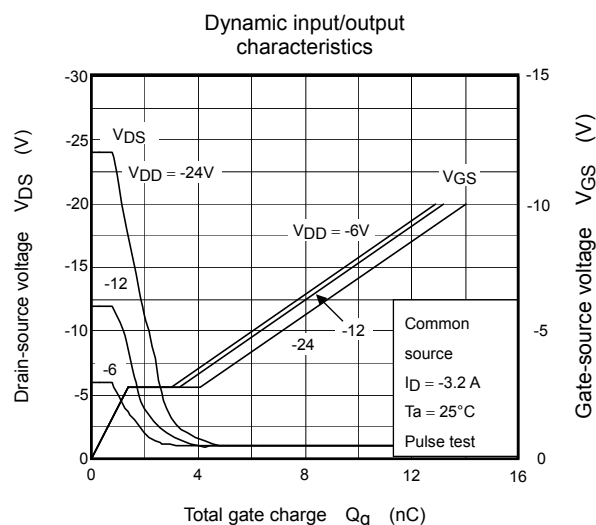
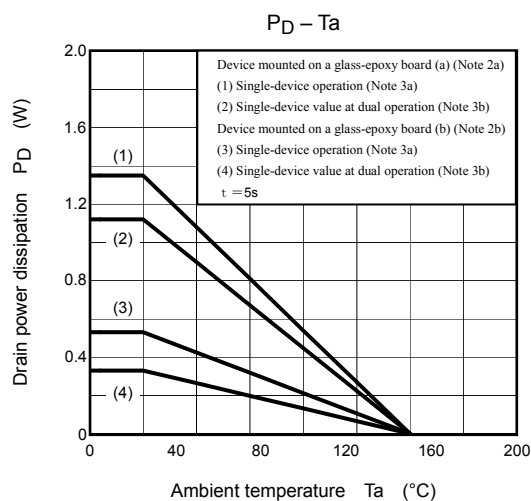
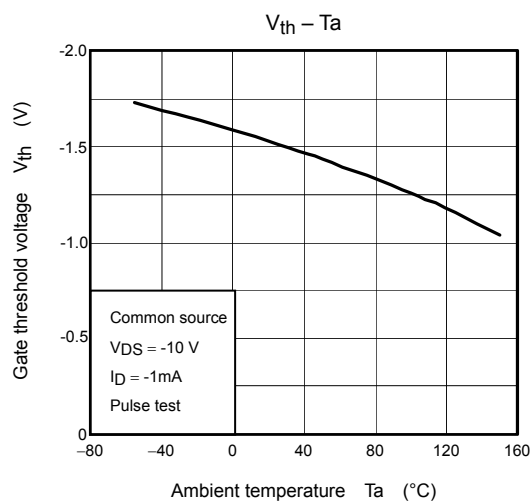
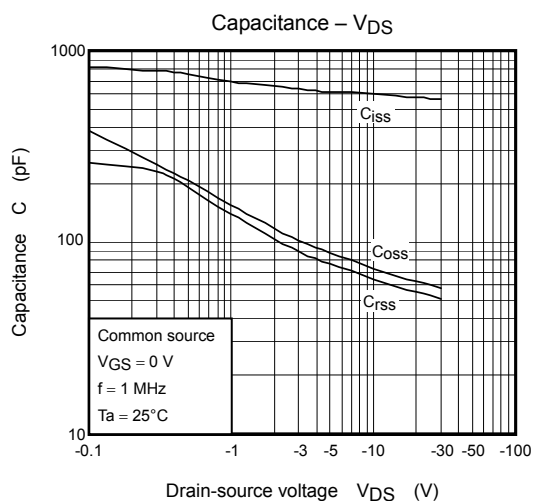
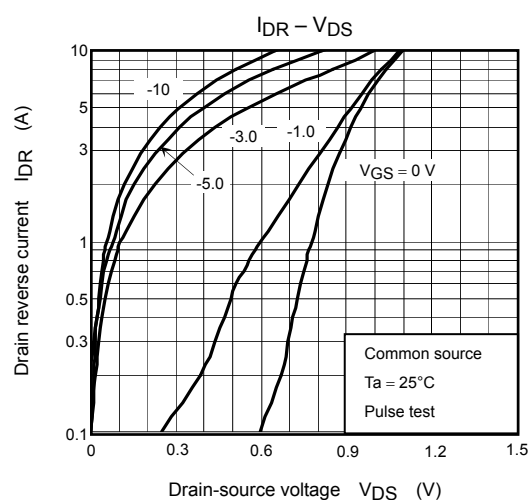
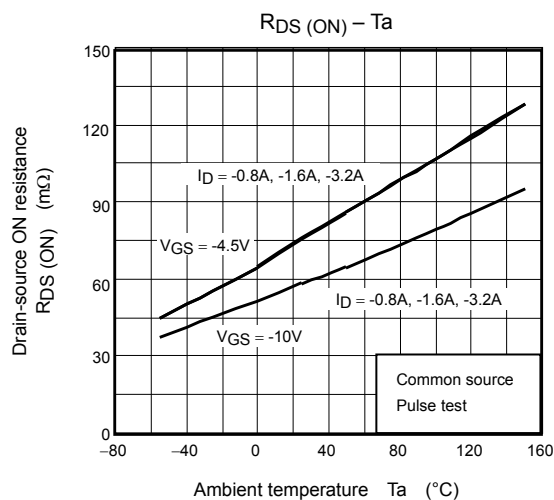
Electrical Characteristics (Ta = 25°C)

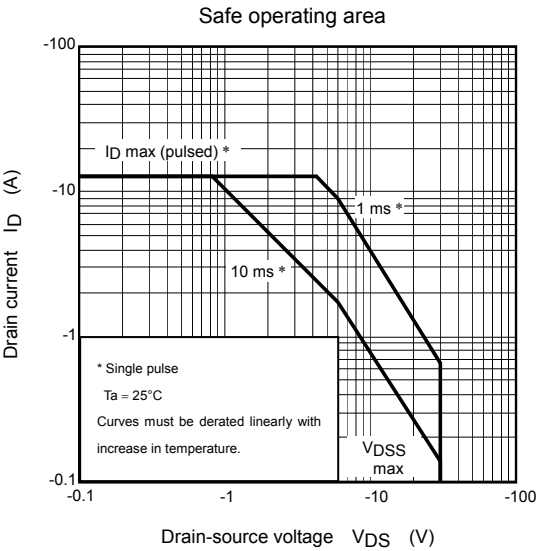
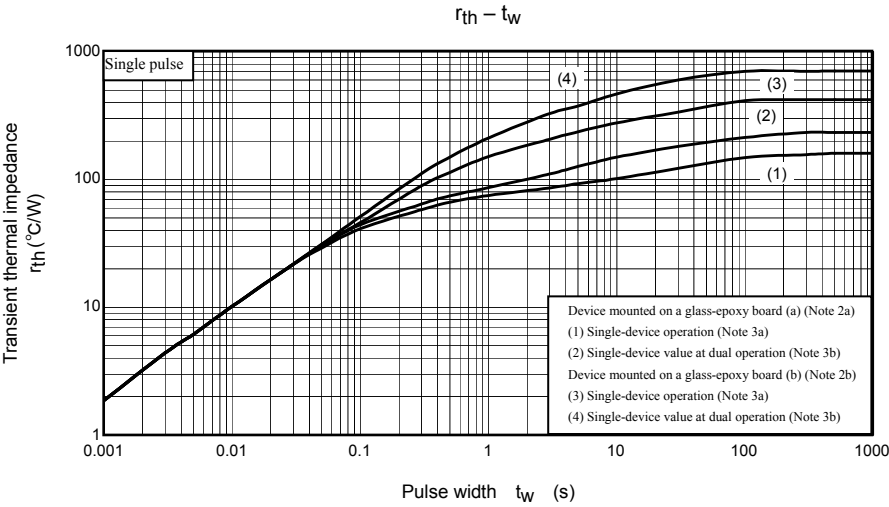
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA
Drain cut-off current		I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V	—	—	-10	μA
Drain-source breakdown voltage		V _(BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-30	—	—	V
		V _(BR) DSX	I _D = -10 mA, V _{GS} = 20 V	-15	—	—	
Gate threshold voltage		V _{th}	V _{DS} = -10 V, I _D = -1 mA	-0.5	—	-1.2	V
Drain-source ON resistance		R _{DS} (ON)	V _{GS} = -4.5 V, I _D = -1.6 A	—	80	105	mΩ
		R _{DS} (ON)	V _{GS} = -10 V, I _D = -1.6 A	—	60	72	
Forward transfer admittance		Y _{fs}	V _{DS} = -10 V, I _D = -1.6 A	2.9	5.9	—	S
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	—	600	—	pF
Reverse transfer capacitance		C _{rss}		—	60	—	
Output capacitance		C _{oss}		—	70	—	
Switching time	Rise time	t _r		—	5.3	—	ns
	Turn-on time	t _{on}		—	12	—	
	Fall time	t _f		—	8.4	—	
	Turn-off time	t _{off}		—	34	—	
Total gate charge (gate-source plus gate-drain)		Q _g	V _{DD} ≈ -24 V, V _{GS} = -10 V, I _D = -3.2 A	—	14	—	nC
Gate-source charge 1		Q _{gs1}		—	1.4	—	
Gate-drain (“Miller”) charge		Q _{gd}		—	2.7	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	-12.8	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = -3.2 \text{ A}$, $V_{GS} = 0 \text{ V}$	—	—	1.2	V







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